

MOSFET - Power, Single N-Channel, SO8-FL

40 V, 0.57 mΩ, 380 A

NTMFS0D6N04XM

Features

- Low R_{DS(on)} to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (5x6 mm) with Compact Design
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Motor Drive
- Battery Protection
- ORing

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V _{DSS}	40	٧
Gate-to-Source Voltage	DC	V_{GS}	±20	V
Continuous Drain Current	T _C = 25°C	I _D	380	Α
	T _C = 100°C		268	
Power Dissipation	T _C = 25°C	P_{D}	150	W
Continuous Drain Current	T _A = 25°C	I _{DA}	61	Α
$R_{ heta JA}$	T _A = 100°C		43	
Pulsed Drain Current	$T_{C} = 25^{\circ}C,$ $t_{p} = 10 \ \mu s$	I _{DM}	2801	Α
Operating Junction and Storage Temperature Range		T _J , T _{STG}	–55 to +175	°C
Source Current (Body Diode)		I _S	125	Α
Single Pulse Avalanche Energy (I _{PK} = 24.9 A)		E _{AS}	562	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		TL	260	°C

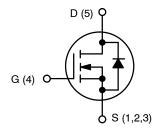
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	1	°C/W
Thermal Resistance, Junction-to-Ambient (Notes 1, 2)	$R_{\theta JA}$	38.8	

- Surface-mounted on FR4 board using 650 mm², 2 oz Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

V _{(BR)DSS}	R _{DS(on)} MAX	I _D MAX
40 V	0.57 m Ω @ 10 V	380 A

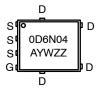


N-CHANNEL MOSFET



DFN5 (SO8-FL) CASE 506FA

MARKING DIAGRAM



0D6N04 = Specific Device Code

A = Assembly Location

Y = Year W = Work Week

ZZ = Lot Traceability

ORDERING INFORMATION

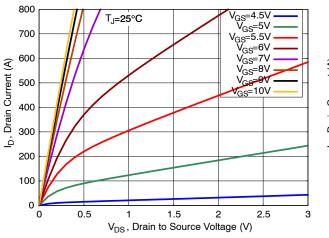
See detailed ordering, marking and shipping information on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		•
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^{\circ}\text{C}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	ΔV _{(BR)DSS} / ΔT _J	I _D = 1 mA, Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, T _J = 25°C			10	μΑ
		V _{DS} = 40 V, T _J = 125°C			100	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
ON CHARACTERISTICS						
Drain-to-Source On Resistance	R _{DS(ON)}	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}, T_J = 25^{\circ}\text{C}$		0.51	0.57	mΩ
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 210 \mu A, T_J = 25^{\circ}C$	2.5	3	3.5	V
Gate Threshold Voltage Temperature Coefficient	ΔV _{GS(TH)} / ΔT _J	$V_{GS} = V_{DS}$, $I_D = 210 \mu A$		-7.26		mV/°C
Forward Trans-conductance	9FS	V _{DS} = 5 V, I _D = 30 A		175		S
CHARGES, CAPACITANCES & GATE RE	SISTANCE					
Input Capacitance	C _{ISS}	V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz		5574		pF
Output Capacitance	C _{OSS}			3887		
Reverse Transfer Capacitance	C _{RSS}			79.5		
Total Gate Charge	Q _{G(TOT)}	V _{DD} = 20 V, I _D = 50 A, V _{GS} = 10 V		86.4		nC
Threshold Gate Charge	Q _{G(TH)}			16.3		
Gate-to-Source Charge	Q _{GS}			24.5		
Gate-to-Drain Charge	Q_{GD}			15.7		
Gate Resistance	R_{G}	f = 1 MHz		5.31		Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	Resistive Load, V _{GS} = 0/10 V,		33.9		ns
Rise Time	t _r	$V_{DD} = 20 \text{ V}, I_D = 50 \text{ A}, R_G = 0 \Omega$		15.6		
Turn-Off Delay Time	t _{d(OFF)}			58.2		
Fall Time	t _f			15.3		
SOURCE-TO-DRAIN DIODE CHARACTE	RISTICS					
Forward Diode Voltage	V _{SD}	$I_S = 30 \text{ A}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$		0.78	1.2	V
		I _S = 30 A, V _{GS} = 0 V, T _J = 125°C		0.63		
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V}, I_{S} = 50 \text{ A},$		77.4		ns
Charge Time	ta	dl/dt = 100 A/μs, V _{DD} = 20 V		41		1
Discharge Time	t _b			36.5		1
Reverse Recovery Charge	Q _{RR}			162		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

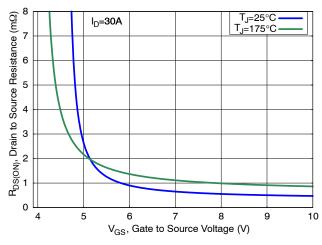


800 V_{DS}=5V
700

(4)
600
400
200
100
200
100
200
100
200
3
4
5
6
7
V_{GS}, Gate to Source Voltage (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



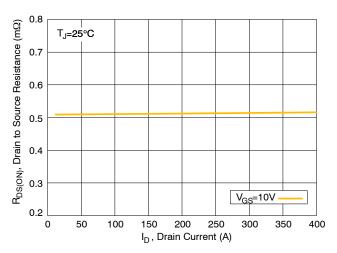
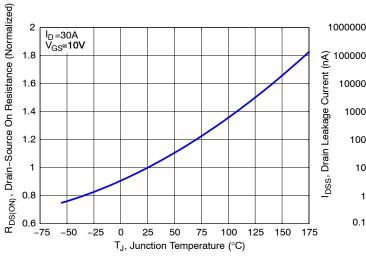


Figure 3. On-Resistance vs. Gate Voltage

Figure 4. On-Resistance vs. Drain Current



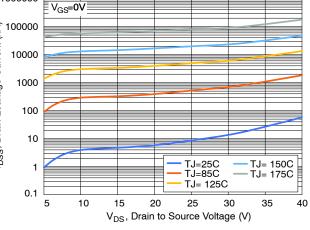
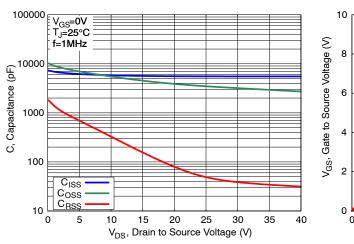


Figure 5. Normalized ON Resistance vs. Junction Temperature

Figure 6. Drain to Source Voltage vs Drain Leakage

TYPICAL CHARACTERISTICS (Continued)

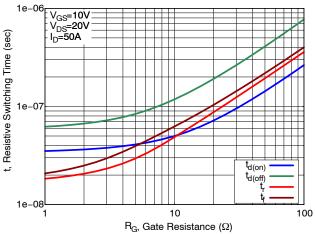
1000



I_D=50A V_{DD}=8V V_{DD}=24V $V_{DD} = 20V$ 0 10 20 30 40 50 60 70 80 100 Q_G, Gate Charge (nC)

Figure 7. Capacitance Characteristics

Figure 8. Gate Charge Characteristics



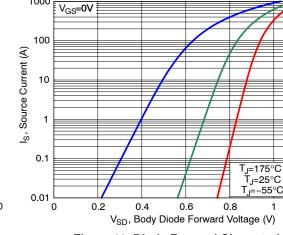
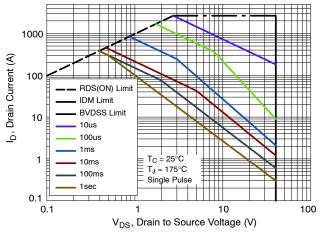


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

Figure 10. Diode Forward Characteristics

1.2



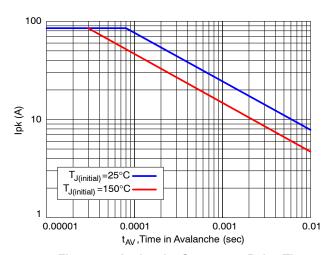


Figure 11. Safe Operating Area (SOA)

Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS (Continued)

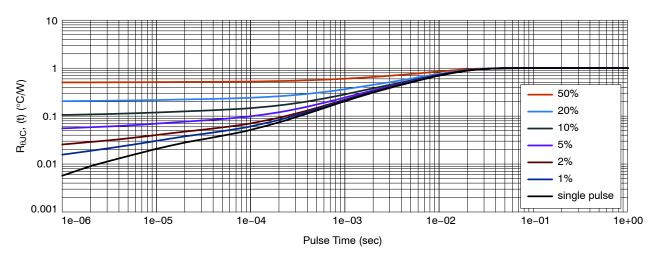


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

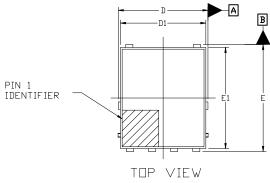
Device	Marking	Package	Shipping [†]
NTMFS0D6N04XMT1G	0D6N04	DFN5 (Pb-Free)	1500 / Tape & Reel

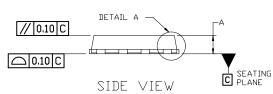
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

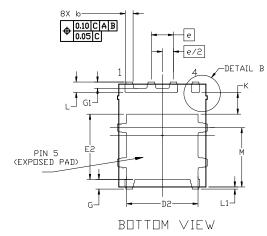
PACKAGE DIMENSIONS

DFN5 5x6, 1.27P

CASE 506FA ISSUE O

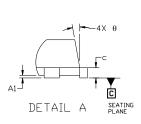




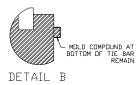


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS 1.
- DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	0.90	1.00	1.10
A1	0.00		0.05
Ø	0.33	0.41	0.51
U	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.80	5.00	5.20
D2	3.90	4.10	4.30
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.55	3.75	3.95
е	1.27 BSC		
G	0.50	0.55	0.70
G1	0.26	0.36	0.46
k	1.10	1.25	1.40
L	0.50	0.60	0.70
L1	0.150 REF		
М	3.00	3.40	3.80
θ	0°		12°



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the IN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

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